



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

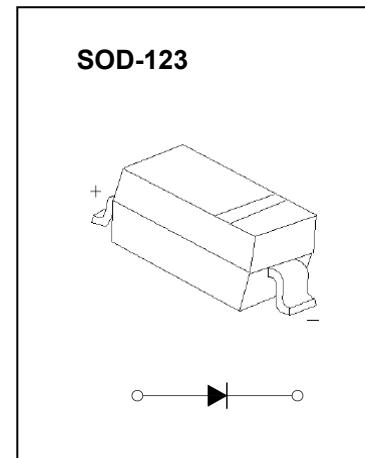
SOD-123 Plastic-Encapsulate Diodes

SD103AW-SD103CW SCHOTTKY BARRIER DIODE

FEATURES

- Low forward voltage drop
- Guard ring construction for transient protection
- Negligible reverse recovery time
- Low reverse capacitance

MARKING: SD103AW: S4
SD103BW: S5
SD103CW: S6



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Peak Repetitive Peak Reverse Voltage	V _{RRM}				
Working Peak Reverse Voltage	V _{RWM}	40	30	20	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	28	21	14	V
Forward Continuous Current	I _{FM}		350		mA
Repetitive Peak Forward Current @t≤1.0s	I _{FRM}		1.5		A
Power Dissipation	P _d		500		mW
Thermal Resistance Junction to Ambient	R _{θJA}		250		°C/W
Junction temperature	T _j		125		°C
Storage Temperature	T _{STG}		-55~+150		°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage SD103AW	V _{(BR)R}	40			V	I _R =100µA
SD103BW		30				I _R =100µA
SD103CW		20				I _R =100µA
Forward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	I _{RM}			5.0	µA	V _R =30V V _R =20V V _R =10V
Capacitance between terminals	C _T		50		pF	V _R =0V,f=1.0MHz
Reverse recovery time	t _{rr}		10		ns	I _F =I _R =200mA I _{rr} =0.1XI _R ,R _L =100Ω